

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Previously presented) A light-emitting diode, comprising:
a semiconductor layer structure including a substrate and at least one light-generating layer formed on said substrate and one transparent current-spreading layer deposited on said light-generating layer, the top surface of said current-spreading layer has vertical structuring to improve the decoupling of light,
a first electrical contact layer on the back of said substrate, and
a second electrical contact layer comprising a lateral structure by means of which substantially uniform coupling of electrical current into said current-spreading layer can be achieved, said second electrical contact layer is discontinuous and is interconnected by a layer of transparent, conductive material said lateral structure comprising a central contact surface that is directly deposited on said current-spreading layer.
2. (Previously presented) The light-emitting diode as described in claim 1, characterized in that
said second electrical contact layer is a central contact surface and, arranged about said central contact surface, a contact structure that is rotationally symmetrical with respect to the center point of said central contact surface and is composed of relatively narrow contact webs and/or contact points.
3. (Previously presented) The light-emitting diode as described in claim 2, characterized in that
the rotational symmetry is a symmetry represented by a whole number.
- 4-5. (Cancelled)

6. (Previously presented) The light-emitting diode as described in claim 1, characterized in that said second electrical contact layer is arranged on structured and/or unstructured portions of said current-spreading layer.

7. (Previously Presented) The light-emitting diode as described in claim 1, characterized in that
the vertical structuring is in the form of n-sided ($n > 3$) pyramids or frusta of pyramids
cones or frusta of cones.

8. (Previously presented) A method for fabricating a light-emitting diode as described in claim 1, characterized in that

a light-generating layer and thereafter a relatively thick and transparent current-spreading layer are deposited on a substrate and the back of said substrate is provided with a first electrical contact layer,

vertical structuring to improve the decoupling of light is produced in the surface of said current-spreading layer, and

a second electrical contact layer having the desired lateral structure is deposited on the structured top surface of said current-spreading layer.

9. (Previously presented) The method for fabricating a light-emitting diode as described in claim 1, characterized in that

a light-generating layer and thereafter a relatively thick and transparent current-spreading layer are deposited on a substrate and the back of said substrate is provided with a first electrical contact layer,

a second electrical contact layer having the desired lateral structure is deposited on the top surface of said current-spreading layer, and

vertical structuring to improve the decoupling of light is produced in the top surface of said current-spreading layer outside the areas of said second electrical contact layer.

10. (Previously presented) The light emitting diode of claim 2 wherein said central contact surface is a circular contact surface.

11. (Previously presented) The light emitting diode of claim 2 wherein said central contact surface is a square contact surface.

12. (Previously presented) The light emitting diode of claim 3 wherein said rotational symmetry matches the rotational symmetry of the light-emitting diode.

13. (Previously presented) The light emitting diode of claim 7 wherein said n-sided ($n > 3$) pyramids or frusta of pyramids, cones or frusta of cones are regularly arranged.

14. (Previously presented) The light-emitting diode as described in claim 1, wherein said lateral structure comprises a central contact structure and a circumferential contact web arranged about the central contact structure.

15-16. (Cancelled)

17. (Previously Presented) The light emitting diode of claim 1 wherein said lateral structure of said contact layer extends over and directly contacts said vertical structuring of said current-spreading layer.

18. (Cancelled)

19. (Previously Presented) The light-emitting diode of claim 1, wherein the lateral structure is directly deposited on the current-spreading layer.

20. (Previously Presented) The light-emitting diode of claim 14, wherein the central contact structure and the circumferential contact web are directly deposited on the current-spreading layer.

21. (Previously presented) The light-emitting diode as described in claim 1, wherein said substantially uniform coupling includes coupling of electrical current through the middle of the current spreading layer.

22. (Currently amended) A light-emitting diode, comprising:
a semiconductor layer structure including a substrate and at least one light-generating layer formed on said substrate and one transparent current-spreading layer deposited on said light-generating layer, the top surface of said current-spreading layer has vertical structuring to improve the decoupling of light,
a first electrical contact layer on the back of said substrate,
a second electrical contact layer comprising a lateral structure by means of which substantially uniform coupling of electrical current into said current-spreading layer can be achieved, wherein the second electrical contact layer comprises discontinuous portions, and
a layer of transparent, ~~light-conducting~~ conductive material deposited on the second electrical contact layer to interconnect the discontinuous portions of the second electrical contact layer.

23. (Currently amended) The light-emitting diode of claim 22, wherein the transparent, ~~light-conducting~~ conductive material comprises indium tin oxide.

24. (Previously Presented) The light-emitting diode of claim 22, wherein the lateral structure is directly deposited on the current spreading layer.

25. (Currently amended) The light-emitting diode of claim 1, wherein the transparent, ~~conducting~~ conductive material comprises indium tin oxide.